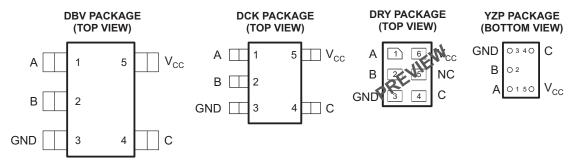
SCES386J-MARCH 2002-REVISED MAY 2007

FEATURES

- Available in the Texas Instruments
 NanoFree™ Package
- Wide V_{CC} Range of 0.8 V to 2.7 V
- Sub-1-V Operable
- Low Power Consumption, 10-μA Max I_{CC}
- High On-Off Output Voltage Ratio
- · High Degree of Linearity
- High Speed Max 0.2 ns (V_{CC} = 1.8 V, C_L = 15 pF)

- Low On-State Impedance Typically 99 Ω (V_{CC} = 2.3 V)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)



See mechanical drawings for dimensions. NC– No internal connection

DESCRIPTION/ORDERING INFORMATION

This single analog switch is operational at 0.8-V to 2.7-V V_{CC} , but is designed specifically for 1.65-V to 1.95-V V_{CC} operation.

The SN74AUC1G66 can handle both analog and digital signals. The combined AC and DC signal has to be between V_{CC} and GND for it to be transmitted in either direction.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

ORDERING INFORMATION

T _A	PACKAGE ⁽¹⁾⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING(3)	
	NanoFree™ WCSP (DSBGA) – YZP (Pb-free)	Reel of 3000	SN74AUC1G66YZAR	U6_	
-40°C to 85°C	SON - DRY	Reel of 5000	SN74AUC1G66DRYR	PREVIEW	
	SOT (SOT-23) - DBV	Reel of 3000	SN74AUC1G66DBVR	U66_	
	SOT (SC-70) - DCK	Reel of 3000	SN74AUC1G66DCKR	U6_	

- Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.
- (2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
- (3) DBV/DCK/DRY: The actual top-side marking has one additional character that designates the assembly/test site. YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

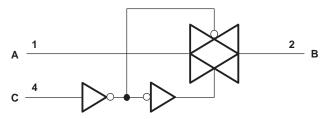
NanoFree is a trademark of Texas Instruments.



FUNCTION TABLE

CONTROL INPUT (C)	SWITCH
L	OFF
Н	ON

LOGIC DIAGRAM (POSITIVE LOGIC)



Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT	
V _{CC}	Supply voltage range		-0.5	3.6	V	
VI	Input voltage range ⁽²⁾	Input voltage range ⁽²⁾			V	
V _{I/O}	Switch I/O voltage range (2)(3)		-0.5	V _{CC} + 0.5	V	
I _{IK}	Control input clamp current	V _I < 0		-50	mA	
I _{IOK}	I/O port diode current	$V_{I/O} < 0$ or $V_{I/O} > V_{CC}$		±50	mA	
I _T	On-state switch current	$V_{I/O} = 0$ to V_{CC}		±50	mA	
	Continuous current through V _{CC} or GND			±100	mA	
		DBV package		206		
0	Dealer at the second improved a sec (4)	DCK package		252	°C/W	
θ_{JA}	Package thermal impedance (4)	DRY package		234	°C/VV	
		YZP package		123		
T _{stg}	Storage temperature range		-65	150	°C	

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

⁽²⁾ All voltages are with respect to ground, unless otherwise specified.

⁽³⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽⁴⁾ The package thermal impedance is calculated in accordance with JESD 51-7.

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Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		0.8	2.7	V
		V _{CC} = 0.8 V	V _{CC}		
V_{IH}	High-level input voltage	$V_{CC} = 1.1 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$		V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		
		$V_{CC} = 0.8 \text{ V}$		0	
V_{IL}	' _{IL} Low-level input voltage	$V_{CC} = 1.1 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	
V _{I/O}	I/O port voltage		0	V_{CC}	V
VI	Control input voltage		0	3.6	V
Δt/Δν	Input transition rise or fall rate			20	ns/V
T _A	Operating free-air temperature		-40	85	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITI	ONS	V _{cc}	MIN TYP(1)	MAX	UNIT
		$V_I = V_{CC}$ or GND,	I _S = 4 mA	1.65 V	10	20	_
r _{on}	On-state switch resistance	V _C = V _{IH} (see Figure 1)	$I_S = 8 \text{ mA}$	2.3 V	9	15	Ω
		$V_I = V_{CC}$ to GND,	$I_S = 4 \text{ mA}$	1.65 V	32	80	
r _{on(p)}	Peak on resistance	V _C = V _{IH} (see Figure 1)	$I_S = 8 \text{ mA}$	2.3 V	15	20	Ω
	$V_I = V_{CC}$ and $V_O = GN$		or			±1	
I _{S(off)}	Off-state switch leakage current	$V_I = GND \text{ and } V_O = V_{CC},$ $V_C = V_{IL} \text{ (see Figure 2)}$		2.7 V		±0.1 ⁽¹⁾	μΑ
	On atota quitab lagkaga gurrant	$V_I = V_{CC}$ or GND, $V_C = V_I$	_H , V _O = Open	2.7 V		±1	
I _{S(on)}	On-state switch leakage current	(see Figure 3)		2.7 V		μΑ	
I _I	Control input current	$V_I = V_{CC}$ or GND		0 to 2.7 V		±5	μΑ
I _{CC}	Supply current	$V_I = V_{CC}$ or GND,	$I_O = 0$	0.8 V to 2.7 V		10	μΑ
C _{ic}	Control input capacitance			2.5 V	2		pF
C _{io(off)}	Switch input/output capacitance			2.5 V	3.5		pF
C _{io(on)}	Switch input/output capacitance			2.5 V	7		pF

⁽¹⁾ All typical values are at $T_A = 25^{\circ}C$.

Switching Characteristics

over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 4)

PARAMETER	PARAMETER FROM TO (INPUT) (OUTPUT)		V _{CC} = 0.8 V	V _{CC} = ± 0.		V _{CC} = ± 0.			_C = 1.8 : 0.15 V		V _{CC} = ± 0.		UNIT
	(INPOT) (OUTPOT)	TYP	MIN	MAX	MIN	MAX	MIN	TYP	MAX	MIN	MAX		
t _{pd} ⁽¹⁾	A or B	B or A	0.9		0.3		0.2			0.2		0.1	ns
t _{en}	С	A or B	4.1	0.5	2.6	0.5	1.7	0.5	0.8	1.1	0.5	1	ns
t _{dis}	С	A or B	5	0.7	3.6	0.5	2.6	0.5	1.7	2.9	0.5	2.2	ns

⁽¹⁾ The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

SN74AUC1G66 SINGLE BILATERAL ANALOG SWITCH

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Switching Characteristics

over recommended operating free-air temperature range, $C_L = 30 \text{ pF}$ (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	۷ _C	_C = 1.8 : 0.15 V	V '	V _{CC} = 2.5 V ± 0.2 V		UNIT
	(INPOT)	(001701)	MIN	TYP	MAX	MIN	MAX	
t _{pd} ⁽¹⁾	A or B	B or A			0.3		0.3	ns
t _{en}	С	A or B	0.5	1.4	2.3	0.8	1.4	ns
t _{dis}	С	A or B	0.5	1.7	2.9	0.5	1.5	ns

⁽¹⁾ The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).



Analog Switch Characteristics

 $T_A = 25^{\circ}C$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	v _{cc}	TYP	UNIT
				V 8.0	60	
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	1.1 V	60	
			f _{in} = sine wave	1.4 V	80	
			(see Figure 5)	1.65 V	120	
Frequency response ⁽¹⁾	A or B	B or A		2.3 V	170	MHz
(switch ON)	AUB	BUIA		V 8.0	>500	IVITIZ
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	1.1 V	>500	
			f _{in} = sine wave	1.4 V	>500	
			(see Figure 5)	1.65 V	>500	
				2.3 V	>500	
				V 8.0	9	
		$C_L = 50 \text{ pF}, R_L = 600 \Omega,$		1.1 V	14	
Crosstalk (control input to signal output)	С	A or B	f _{in} = 1 MHz (square wave)	1.4 V	15	mV
(common impart to diginal datpat)			(see Figure 6)	1.65 V	16	
				2.3 V	20	
				0.8 V	-60	dB
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	1.1 V	-60	
	A B	B or A	f _{in} = 1 MHz (sine wave) (see Figure 7)	1.4 V	-60	
				1.65 V	-60	
Feedthrough attenuation (2)				2.3 V	-60	
(switch OFF)	A or B			0.8 V	-55	
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	1.1 V	-55	
			f _{in} = 1 MHz (sine wave)	1.4 V	-55	
			(see Figure 7)	1.65 V	-55	
				2.3 V	-55	
				0.8 V	7.5	
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$	1.1 V	0.16	
	A or B	B or A	f _{in} = 1 kHz (sine wave)	1.4 V	0.04	
			(see Figure 8)	1.65 V	0.03	
Cina waya diatartis				2.3 V	0.02	0/
Sine-wave distortion				0.8 V	4.2	%
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$	1.1 V	0.2	
	A or B	B or A	f _{in} = 10 kHz (sine wave)	1.4 V	0.03	
			(see Figure 8)	1.65 V	0.02	
				2.3 V	0.02	

⁽¹⁾ Adjust f_{in} voltage to obtain 0 dBm at output. Increase f_{in} frequency until dB meter reads -3 dB. (2) Adjust f_{in} voltage to obtain 0 dBm at input.

Operating Characteristics

 $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	V _{CC} = 0.8 V TYP	V _{CC} = 1.2 V TYP	V _{CC} = 1.5 V TYP	V _{CC} = 1.8 V TYP	V _{CC} = 2.5 V TYP	UNIT
C _{pd}	Power dissipation capacitance	f = 10 MHz	3	3	3	3	3	pF



PARAMETER MEASUREMENT INFORMATION

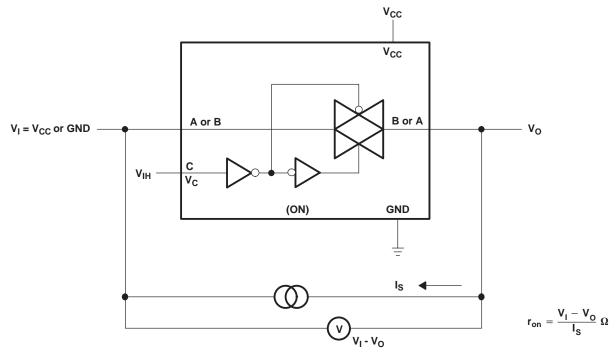


Figure 1. On-State Resistance Test Circuit

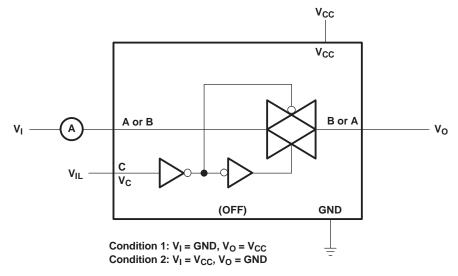


Figure 2. Off-State Switch Leakage-Current Test Circuit



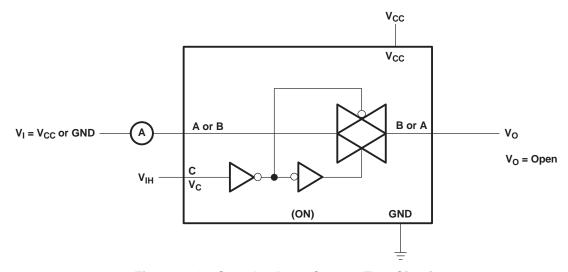
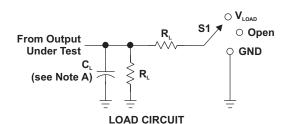


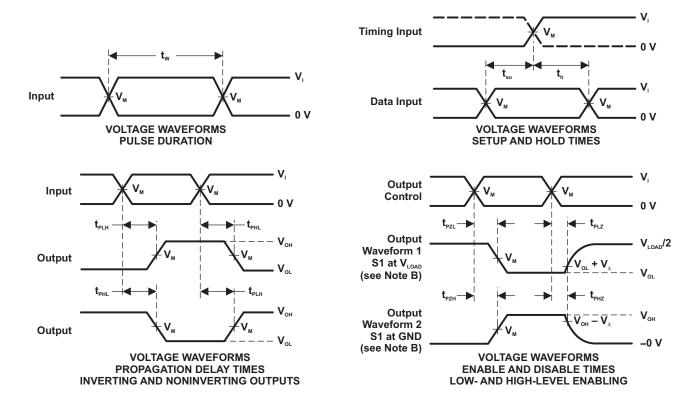
Figure 3. On-State Leakage-Current Test Circuit





TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

V	INPUTS		V	V	•	Б	
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _∟	$R_{\scriptscriptstyle L}$	$\mathbf{V}_{_{\Delta}}$
0.8 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	2 kΩ	0.1 V
1.2 V ± 0.1 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	2 k Ω	0.1 V
1.5 V ± 0.1 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	2 k Ω	0.1 V
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	2 k Ω	0.15 V
2.5 V ± 0.2 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	2 k Ω	0.15 V
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V
2.5 V ± 0.2 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \Omega$,
- D. The outputs are measured one at a time, with one transition per measurement.
- E. $t_{\mbox{\tiny PLZ}}$ and $\dot{t}_{\mbox{\tiny PHZ}}$ are the same as $t_{\mbox{\tiny dis}}.$
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. $t_{\text{\tiny PLH}}$ and $t_{\text{\tiny PHL}}$ are the same as $t_{\text{\tiny pd}}$.

Figure 4. Load Circuit and Voltage Waveforms



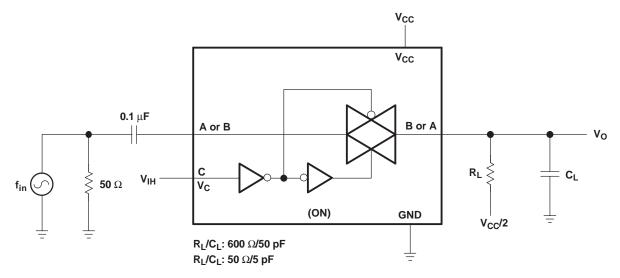


Figure 5. Frequency Response (Switch ON)

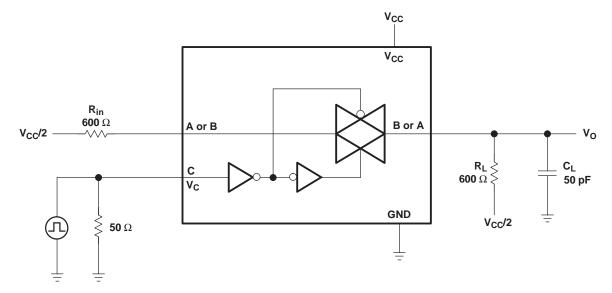


Figure 6. Crosstalk (Control Input – Switch Output)



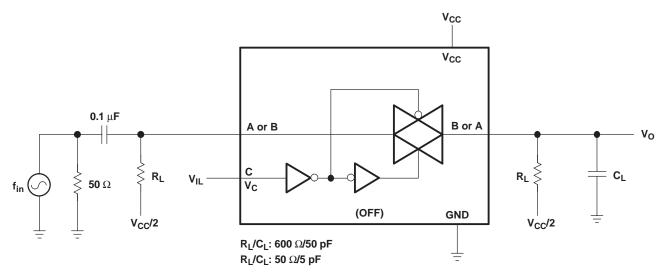


Figure 7. Feedthrough (Switch OFF)

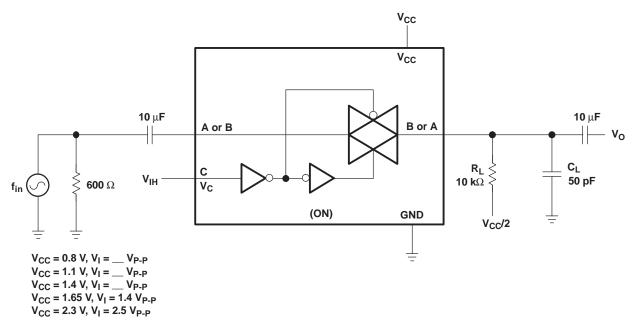


Figure 8. Sine-Wave Distortion





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PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN74AUC1G66DBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUC1G66DBVRE4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUC1G66DBVRG4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUC1G66DCKR	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUC1G66DCKRE4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUC1G66DCKRG4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUC1G66YZPR	ACTIVE	WCSP	YZP	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

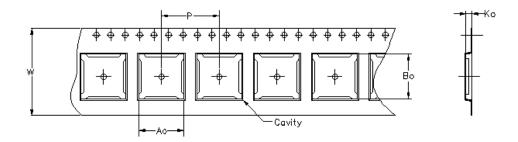
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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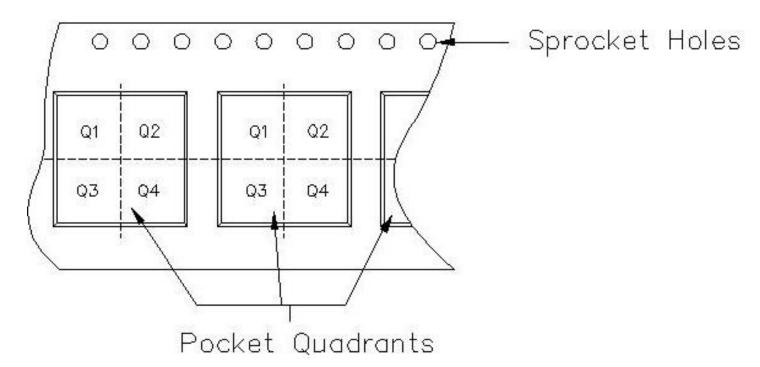
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Carrier tape design is defined largely by the component lentgh, width, and thickness.

Ao =	Dimension	designed	to	accommodate	the	component	width.
Bo =	Dímension	designed	to	accommodate	the	component	length.
Ko =	Dímension	designed	to	accommodate	the	component	thickness.
W =	Overall widt	h of the	car	rier tape.			
P = Pitch between successive cavity centers.							



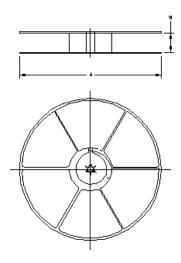
TAPE AND REEL INFORMATION



PACKAGE MATERIALS INFORMATION

19-May-2007

Device	Package	Pins	Site	Reel Diameter (mm)	Reel Width (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AUC1G66DBVR	DBV	5	HNT	180	9	3.23	3.17	1.37	4	8	Q3
SN74AUC1G66DCKR	DCK	5	HNT	180	9	2.24	2.34	1.22	4	8	Q3
SN74AUC1G66YZPR	YZP	5	ASEK	180	8	1.02	1.52	0.66	4	8	Q1



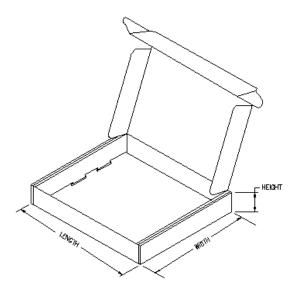
TAPE AND REEL BOX INFORMATION

Device	Package	Pins	Site	Length (mm)	Width (mm)	Height (mm)
SN74AUC1G66DBVR	DBV	5	HNT	202.0	201.0	28.0
SN74AUC1G66DCKR	DCK	5	HNT	202.0	201.0	28.0
SN74AUC1G66YZPR	YZP	5	ASEK	220.0	220.0	34.0





19-May-2007



DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-178 Variation AA.



DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



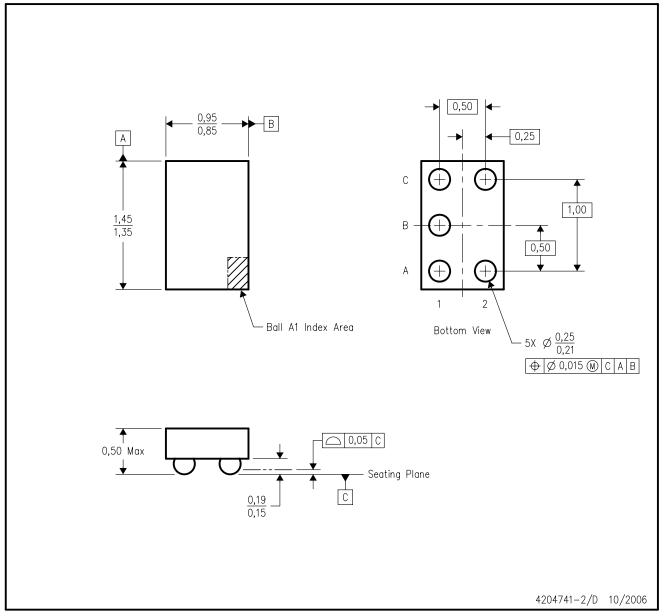
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.



YZP (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. NanoFree $^{\text{TM}}$ package configuration.
- D. This package is lead-free. Refer to the 5 YEP package (drawing 4204725) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.



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